

Plastic-Encapsulate Transistors

TRANSISTOR (NPN)

FEATURES

- Small Flat Package
- High Speed Switching Time
- Low Collector-emitter saturation voltage
- Complementary to 2SA1213

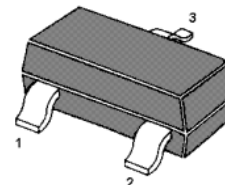
APPLICATIONS

- Power Amplifier and Switching

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	50	V
V_{CE0}	Collector-Emitter Voltage	50	V
V_{EB0}	Emitter-Base Voltage	5	V
I_C	Collector Current	2	A
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	$^{\circ}\text{C/W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=50\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2\text{V}, I_C=0.5\text{A}$	70		240	
	$h_{FE(2)}$	$V_{CE}=2\text{V}, I_C=2\text{A}$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1\text{A}, I_B=50\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=1\text{A}, I_B=50\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE}=2\text{V}, I_C=0.5\text{A}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		30		pF

CLASSIFICATION OF $h_{FE(1)}$

RANK	O	Y
RANGE	70 - 140	120 - 240
MARKING	MO	MY

Typical Characteristics

